

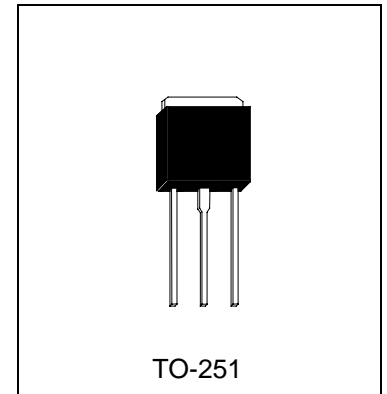


# HBT134XI Series

TRIAC, LOGIC LEVEL & STANDARD

## Description

Passivated, sensitive gate triacs in a plastic envelope, intended for use in general purpose bidirectional switching and phase control applications, where high sensitivity is required in all four quadrants.



## Quick Reference Data

Part No.	$V_{DRM}(V)$	$I_{T(RMS)}(A)$	$I_{TSM}(A)$	Quadrant
HBT134CI	600	4	30	All
HBT134DI	600	4	30	I - II - III
HBT134GI	800	4	30	All
HBT134HI	800	4	30	I - II - III

## Pin Configuration

Pin	Description	Symbol
1	Main terminal 1	
2	Main terminal 2	
3	Gate	

## Limiting Values

Symbol	Parameter	Min.	Max.	Units
$V_{DRM}$	HBT134CI / DI Repetitive peak off-state voltages	-	600	V
	HBT134GI / HI Repetitive peak off-state voltages	-	800	V
$I_{T(RMS)}$	RMS on-state current	-	4	A
$I_{TSM}$	Non-repetitive peak on-state current	-	30	A
$I^2t$	$I^2t$ for fusing	-	3.7	A <sup>2</sup> S
$dI_T/dt$	Repetitive rate of rise of on-state current after triggering T2+ G+	-	50	A/us
	T2+ G-	-	50	A/us
	T2- G-	-	50	A/us
	T2- G+ (HBT134DI / HI without this quadrant)	-	10	A/us
$I_{GM}$	Peak gate current	-	1	A
$V_{GM}$	Peak gate voltage	-	7	V
$P_{GM}$	Peak gate power	-	1.5	W
$P_{G(AV)}$	Average gate power	-	0.1	W
Tstg	Storage Temperature Range	-	150	°C
Tj	Operating junction temperature	-40	125	°C



**HBT134CI / HBT134GI**

**Electrical Characteristics** (Ta=25°C, unless otherwise stated, 4 Quadrant)

Symbol	Parameter	Conditions	Rank		Unit
			T	U	
I <sub>GT</sub>	Gate Trigger Current	V <sub>D</sub> =6V, R <sub>L</sub> =10Ω, T2+ G+	5	10	mA
		V <sub>D</sub> =6V, R <sub>L</sub> =10Ω, T2+ G-	5	10	mA
		V <sub>D</sub> =6V, R <sub>L</sub> =10Ω, T2- G-	5	10	mA
		V <sub>D</sub> =6V, R <sub>L</sub> =10Ω, T2- G+	10	25	mA
I <sub>L</sub>	Latching Current	V <sub>D</sub> =6V, R <sub>L</sub> =10Ω, T2+ G+	15	15	mA
		V <sub>D</sub> =6V, R <sub>L</sub> =10Ω, T2+ G-	20	20	mA
		V <sub>D</sub> =6V, R <sub>L</sub> =10Ω, T2- G-	15	15	mA
		V <sub>D</sub> =6V, R <sub>L</sub> =10Ω, T2- G+	20	20	mA
I <sub>H</sub>	Holding Current	V <sub>D</sub> =12V, I <sub>GT</sub> =0.1A	15	15	mA
V <sub>T</sub>	On-state Voltage	I <sub>T</sub> =4.5A	1.5	1.5	V
V <sub>GT</sub>	Gate Trigger Voltage	V <sub>D</sub> =6V, R <sub>L</sub> =10Ω, T2+ G+	1.5	1.5	V
		V <sub>D</sub> =6V, R <sub>L</sub> =10Ω, T2+ G-	1.5	1.5	V
		V <sub>D</sub> =6V, R <sub>L</sub> =10Ω, T2- G-	1.5	1.5	V
		V <sub>D</sub> =6V, R <sub>L</sub> =10Ω, T2- G+	1.8	1.8	V
I <sub>D</sub>	Off-state Leakage Current	V <sub>D</sub> =V <sub>DRM</sub>	200	200	uA

**HBT134DI / HBT134HI**

**Electrical Characteristics** (Ta=25°C, unless otherwise stated, 3 Quadrant)

Symbol	Parameter	Conditions	Rank		Unit
			T	U	
I <sub>GT</sub>	Gate Trigger Current	V <sub>D</sub> =6V, R <sub>L</sub> =10Ω, T2+ G+	5	10	mA
		V <sub>D</sub> =6V, R <sub>L</sub> =10Ω, T2+ G-	5	10	mA
		V <sub>D</sub> =6V, R <sub>L</sub> =10Ω, T2- G-	5	10	mA
		V <sub>D</sub> =6V, R <sub>L</sub> =10Ω, T2- G+	-	-	mA
I <sub>L</sub>	Latching Current	V <sub>D</sub> =6V, R <sub>L</sub> =10Ω, T2+ G+	15	15	mA
		V <sub>D</sub> =6V, R <sub>L</sub> =10Ω, T2+ G-	20	20	mA
		V <sub>D</sub> =6V, R <sub>L</sub> =10Ω, T2- G-	15	15	mA
		V <sub>D</sub> =6V, R <sub>L</sub> =10Ω, T2- G+	-	-	mA
I <sub>H</sub>	Holding Current	V <sub>D</sub> =12V, I <sub>GT</sub> =0.1A	15	15	mA
V <sub>T</sub>	On-state Voltage	I <sub>T</sub> =4.5A	1.5	1.5	V
V <sub>GT</sub>	Gate Trigger Voltage	V <sub>D</sub> =6V, R <sub>L</sub> =10Ω, T2+ G+	1.5	1.5	V
		V <sub>D</sub> =6V, R <sub>L</sub> =10Ω, T2+ G-	1.5	1.5	V
		V <sub>D</sub> =6V, R <sub>L</sub> =10Ω, T2- G-	1.5	1.5	V
		V <sub>D</sub> =6V, R <sub>L</sub> =10Ω, T2- G+	-	-	V
I <sub>D</sub>	Off-state Leakage Current	V <sub>D</sub> =V <sub>DRM</sub>	200	200	uA



### Static Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$dV_D/dt$	Critical rate of rise of off-state voltage	$V_{DM}=67\% V_{DRM(max)}$ ; $T_j=125^\circ C$ ; exponential waveform; gate open circuit	-	50	-	V/us
tgt	Gate controlled turn-on time	$I_{TM}=6A$ ; $V_D=V_{DRM(max)}$ ; $I_G=0.1A$ ; $dI_G/dt=5A/us$	-	2	-	us

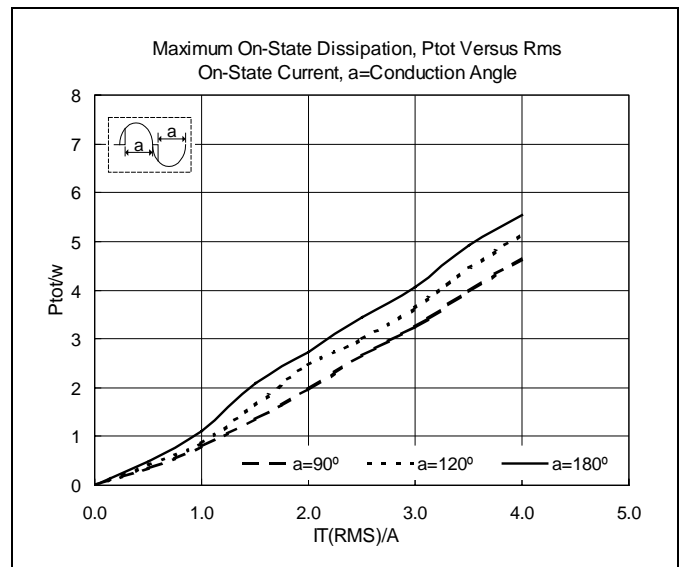
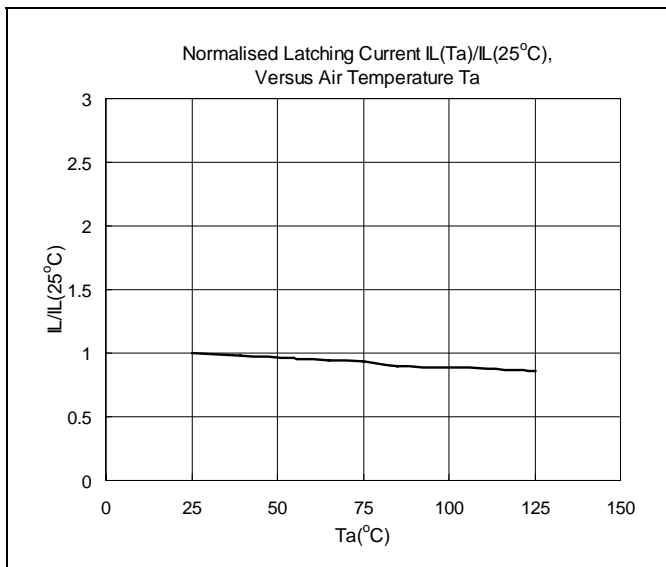
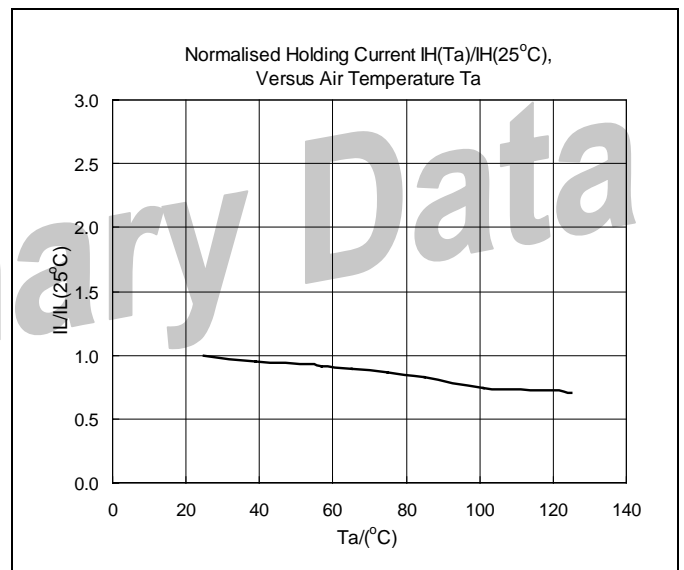
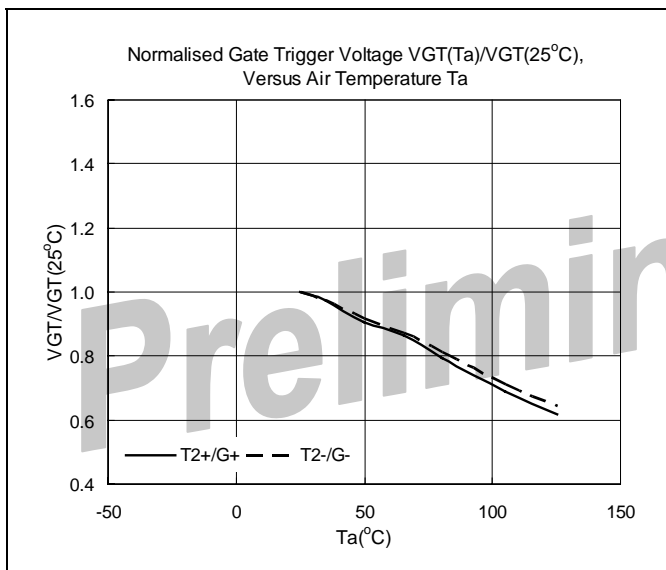
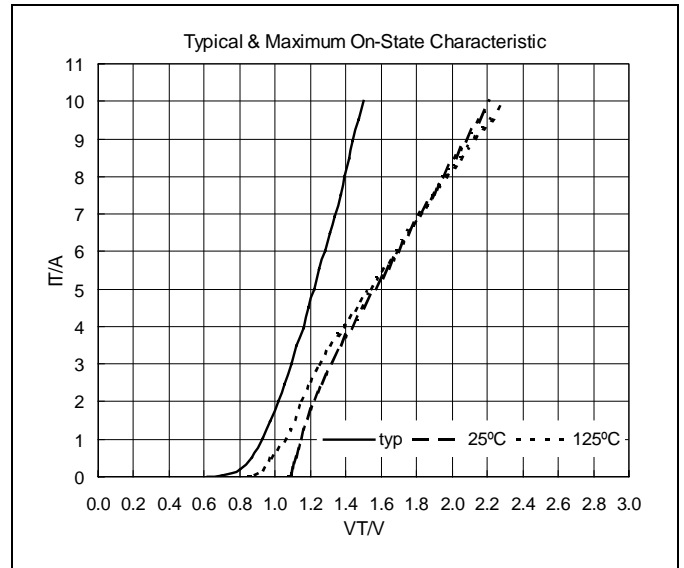
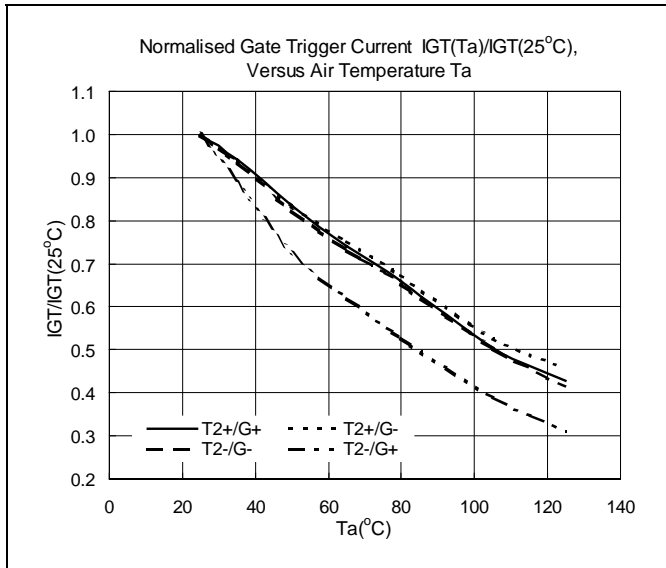
### Thermal Resistances

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Rth j-mb	Thermal resistance junction to mounting base	Full cycle	-	-	3.0	K/W
		Half cycle	-	-	3.7	K/W
Rth j-a	Thermal resistance junction to ambient	In free air	-	60	-	K/W

Preliminary Data

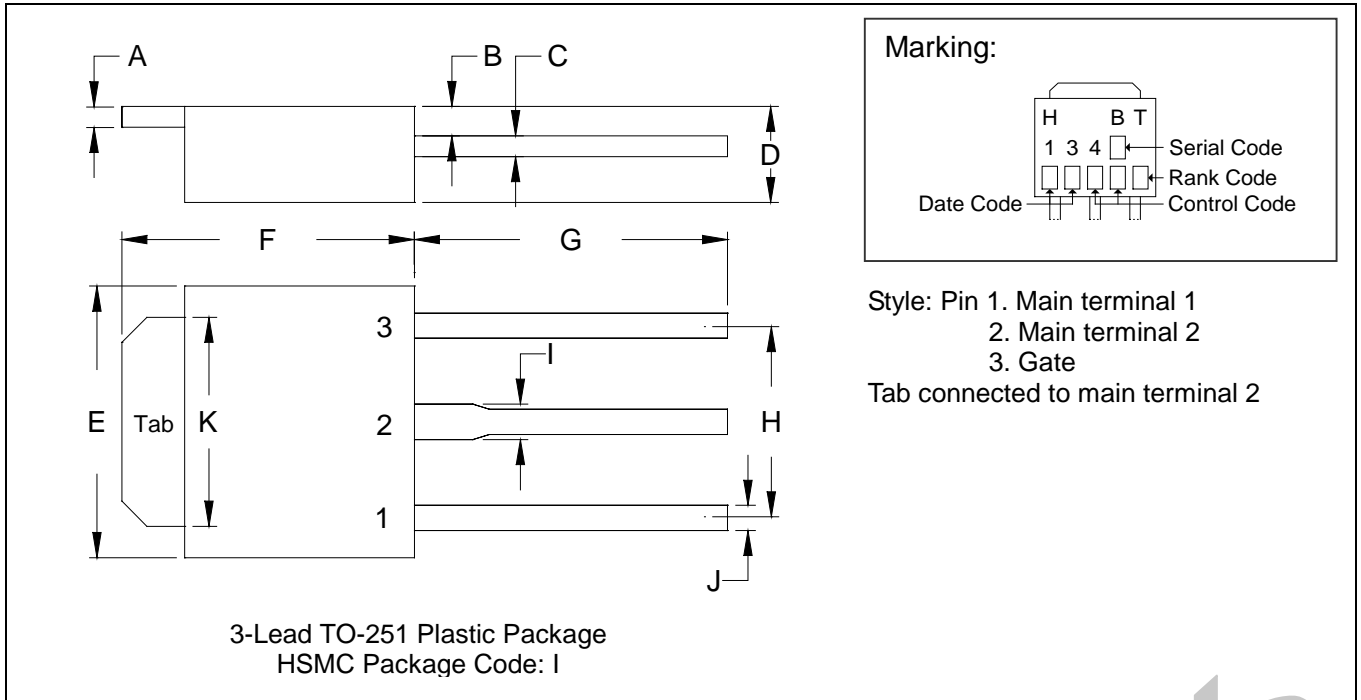


### Characteristics Curve





### TO-251 Dimension



\*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.0177	0.0217	0.45	0.55	G	0.2559	-	6.50	-
B	0.0354	0.0591	0.90	1.50	H	-	*0.1811	-	*4.60
C	0.0177	0.0236	0.45	0.60	I	-	0.0354	-	0.90
D	0.0866	0.0945	2.20	2.40	J	-	0.0315	-	0.80
E	0.2520	0.2677	6.40	6.80	K	0.2047	0.2165	5.20	5.50
F	0.2677	0.2835	6.80	7.20					

**Notes:** 1.Dimension and tolerance based on our Spec. dated May. 24,1995.  
 2.Controlling dimension: millimeters.  
 3.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.  
 4.If there is any question with packing specification or packing method, please contact your local HSMC sales office.

**Material:**

- Lead: 42 Alloy ; solder plating
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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